**Product data sheet** 

## 1. General description

Hyperfast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

### 2. Features and benefits

- · Fast switching
- Surface-mountable package
- · Low leakage current
- · Low reverse recovery current
- · Low thermal resistance
- Reduces switching losses in associated MOSFET

## 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 130 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	8	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 µs; $T_{mb} \le 130$ °C; square-wave pulse	-	-	16	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	91	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	100	Α
Static charac	cteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.4	-	V
Dynamic cha	racteristics					,
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; $\frac{\text{Fig. 7}}{}$	-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns

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**BYC8B-600P** 

Hyperfast power diode

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection	mb	K — A
2	K	cathode[1]		001aaa020
3	Α	anode		
mb	К	mounting base; connected to cathode	D2PAK (SOT404)	

<sup>[1]</sup> It is not possible to connect to pin 2 of the SOT404 package.

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	age					
	Name	Description	Version				
BYC8B-600P	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

## 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
BYC8B-600P	BYC8B-600P

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## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 130 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	8	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le 130$ °C; square-wave pulse	-	16	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	А
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

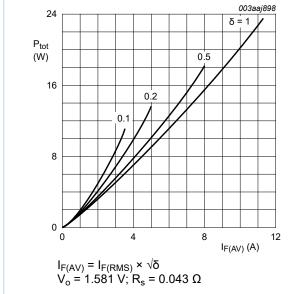


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

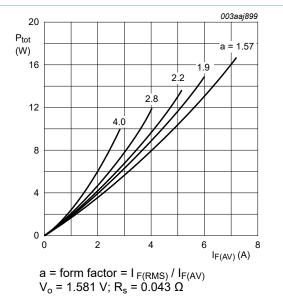


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

### Hyperfast power diode

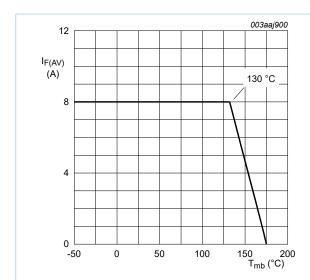


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

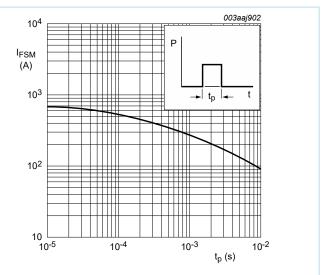


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

Hyperfast power diode

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

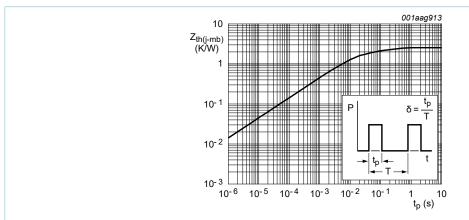


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

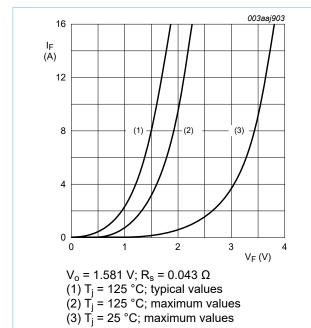
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### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.4	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	20	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	200	μΑ
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 200 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	Α
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	-	6	Α
Q <sub>r</sub>	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 ^{\circ}\text{C}; Fig. 7$	-	90	-	nC





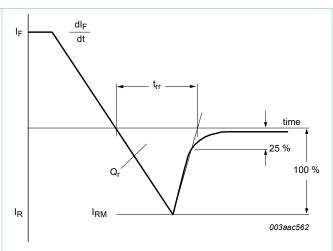
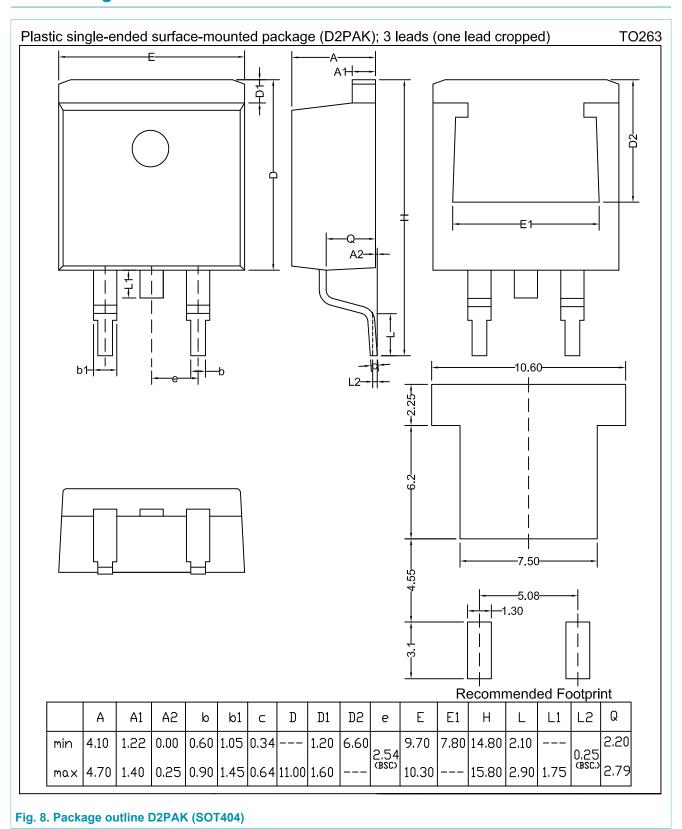


Fig. 7. Reverse recovery definitions; ramp recovery

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## 11. Package outline



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#### Hyperfast power diode

## 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**BYC8B-600P** 

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